

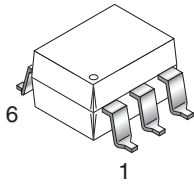
H11AV1-M

H11AV1A-M

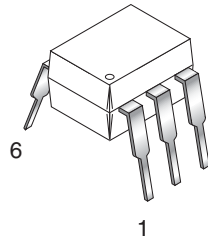
H11AV2-M

H11AV2A-M

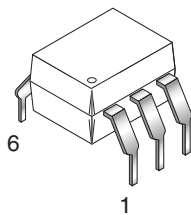
PACKAGE OUTLINE



H11AV1S-M, H11AV2S-M

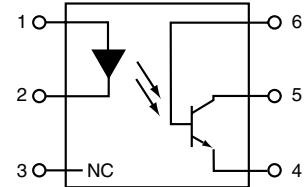


H11AV1-M, H11AV2-M



H11AV1A-M, H11AV2A-M

SCHEMATIC



- PIN 1. ANODE
- 2. CATHODE
- 3. NO CONNECTION
- 4. EMITTER
- 5. COLLECTOR
- 6. BASE

DESCRIPTION

The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line white package.

FEATURES

- H11AV1 and H11AV2 feature 0.3" input-output lead spacing
- H11AV1A and H11AV2A feature 0.4" input-output lead spacing
- UL recognized (File #E90700, Vol. 2)
- VDE recognized (File #102497)
- Add option V (e.g., H11AV1AV-M)

APPLICATIONS

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

H11AV1-M

H11AV1A-M

H11AV2-M

H11AV2A-M

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified) | | | |
|--|------------------|----------------|----------------------|
| Parameter | Symbol | Value | Units |
| TOTAL DEVICE | | | |
| Storage Temperature | T_{STG} | -40 to +150 | $^\circ\text{C}$ |
| Operating Temperature | T_{OPR} | -40 to +100 | $^\circ\text{C}$ |
| Wave solder temperature (see page 9 for reflow solder profiles) | T_{SOL} | 260 for 10 sec | $^\circ\text{C}$ |
| Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ | P_D | 250 | mW |
| Derate above 25°C | | 2.94 | mW/ $^\circ\text{C}$ |
| EMITTER | | | |
| DC/Average Forward Input Current | I_F | 60 | mA |
| Reverse Input Voltage | V_R | 6 | V |
| LED Power Dissipation @ $T_A = 25^\circ\text{C}$ | P_D | 120 | mW |
| Derate above 25°C | | 1.41 | mW/ $^\circ\text{C}$ |
| DETECTOR | | | |
| Collector-Emitter Voltage | V_{CEO} | 70 | V |
| Collector-Base Voltage | V_{CBO} | 70 | V |
| Emitter-Collector Voltage | V_{ECO} | 7 | V |
| Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ | P_D | 150 | mW |
| Derate above 25°C | | 1.76 | mW/ $^\circ\text{C}$ |

H11AV1-M

H11AV1A-M

H11AV2-M

H11AV2A-M

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

| Parameter | Test Conditions | Symbol | Min | Typ* | Max | Unit |
|--|--|------------|-----|------|-----|---------------|
| EMITTER | | | | | | |
| Input Forward Voltage ($I_F = 10\text{ mA}$) | $T_A = 25^\circ\text{C}$ | V_F | 0.8 | 1.18 | 1.5 | V |
| | $T_A = -55^\circ\text{C}$ | | 0.9 | 1.28 | 1.7 | |
| | $T_A = 100^\circ\text{C}$ | | 0.7 | 1.05 | 1.4 | |
| Reverse Leakage Current | ($V_R = 6.0\text{ V}$) | I_R | | | 10 | μA |
| DETECTOR | | | | | | |
| Collector-Emitter Breakdown Voltage | ($I_C = 1.0\text{ mA}$, $I_F = 0$) | BV_{CEO} | 70 | 100 | | V |
| Collector-Base Breakdown Voltage | ($I_C = 100\ \mu\text{A}$, $I_F = 0$) | BV_{CBO} | 70 | 120 | | V |
| Emitter-Collector Breakdown Voltage | ($I_E = 100\ \mu\text{A}$, $I_F = 0$) | BV_{ECO} | 7 | 10 | | V |
| Collector-Emitter Dark Current | ($V_{CE} = 10\text{ V}$, $I_F = 0$) | I_{CEO} | | 1 | 50 | nA |
| Collector-Base Dark Current | ($V_{CB} = 10\text{ V}$) | I_{CBO} | | 0.5 | | nA |
| Capacitance | ($V_{CE} = 0\text{ V}$, $f = 1\text{ MHz}$) | C_{CE} | | 8 | | pF |

ISOLATION CHARACTERISTICS

| Characteristic | Test Conditions | Symbol | Min | Typ* | Max | Units |
|--------------------------------|---|-----------|-----------|------|-----|----------|
| Input-Output Isolation Voltage | ($f = 60\text{ Hz}$, $t = 1\text{ sec}$) | V_{ISO} | 7500 | | | Vac(pk) |
| Isolation Resistance | ($V_{I-O} = 500\text{ VDC}$) | R_{ISO} | 10^{11} | | | Ω |
| Isolation Capacitance | ($V_{I-O} = 0\text{ V}$, $f = 1\text{ MHz}$) | C_{ISO} | | 0.2 | 2 | pF |

Note

* Typical values at $T_A = 25^\circ\text{C}$

H11AV1-M

H11AV1A-M

H11AV2-M

H11AV2A-M

TRANSFER CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

| DC Characteristic | Test Conditions | Symbol | Device | Min | Typ* | Max | Unit |
|--|---|---------------|-------------------|-----|------|-----|---------------|
| Current Transfer Ratio, Collector to Emitter | $(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V})$ | CTR | H11AV1 H11AV1A | 100 | | 300 | % |
| | | | H11AV2 H11AV2A | 50 | | | |
| Collector-Emitter Saturation Voltage | $(I_C = 2 \text{ mA}, I_F = 20 \text{ mA})$ | $V_{CE(SAT)}$ | All | | | 0.4 | V |
| AC Characteristic | | | | | | | |
| Non-Saturated Turn-on Time | $(I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig. 11) | T_{ON} | All | | | 15 | μs |
| Non Saturated Turn-off Time | $(I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig. 11) | T_{ON} | All | | | 15 | μs |

* Typical values at $T_A = 25^\circ\text{C}$

TYPICAL PERFORMANCE CURVES

Fig. 1 LED Forward Voltage vs. Forward Current

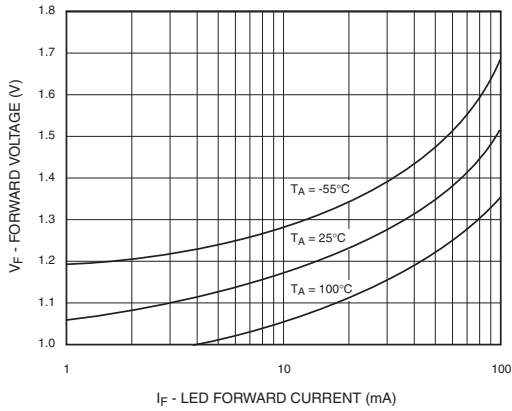


Fig. 2 Normalized CTR vs. Forward Current

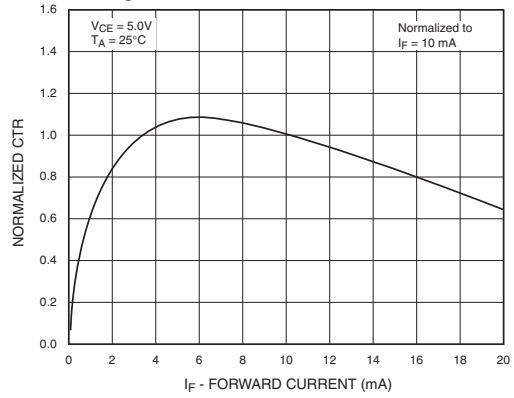


Fig. 3 Normalized CTR vs. Ambient Temperature

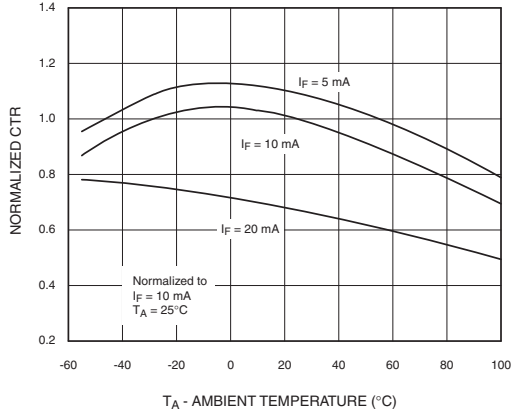


Fig. 4 CTR vs. RBE (Unsaturated)

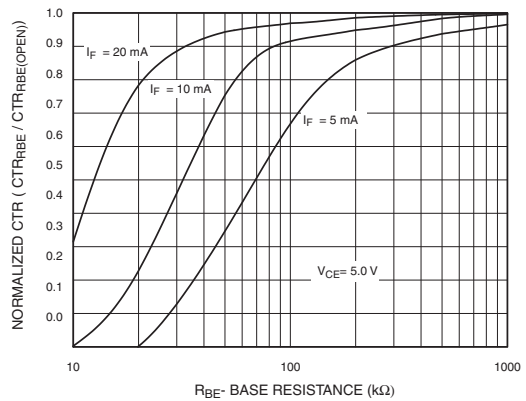


Fig. 5 CTR vs. RBE (Saturated)

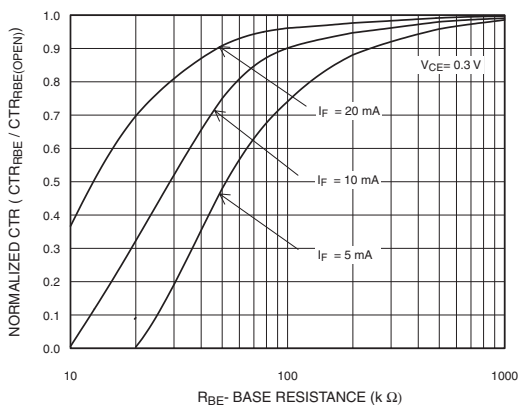
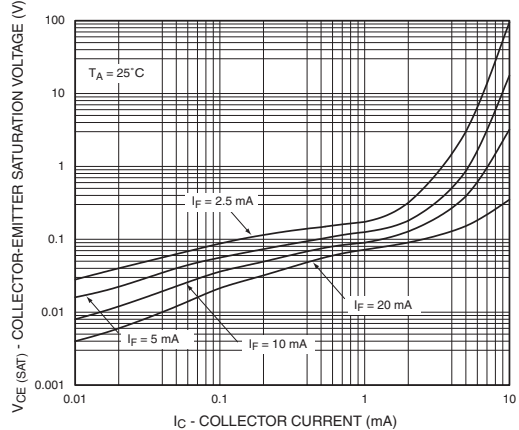


Fig. 6 Collector-Emitter Saturation Voltage vs. Collector Current



H11AV1-M

H11AV1A-M

H11AV2-M

H11AV2A-M

Fig. 7 Switching Speed vs. Load Resistor

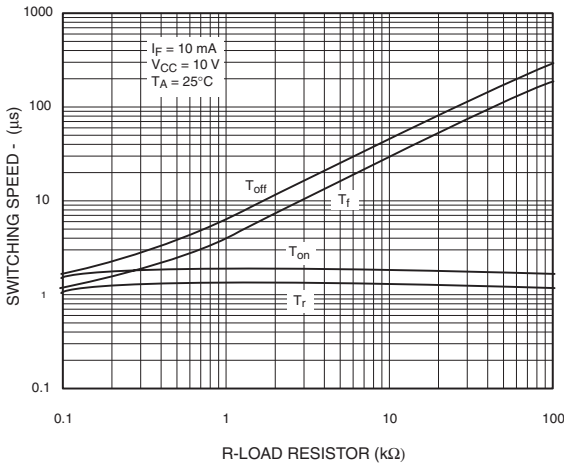


Fig. 8 Normalized t_{on} vs. R_{BE}

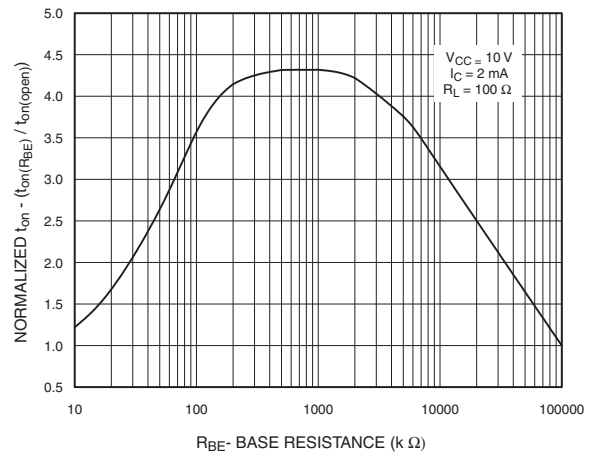


Fig. 9 Normalized t_{off} vs. R_{BE}

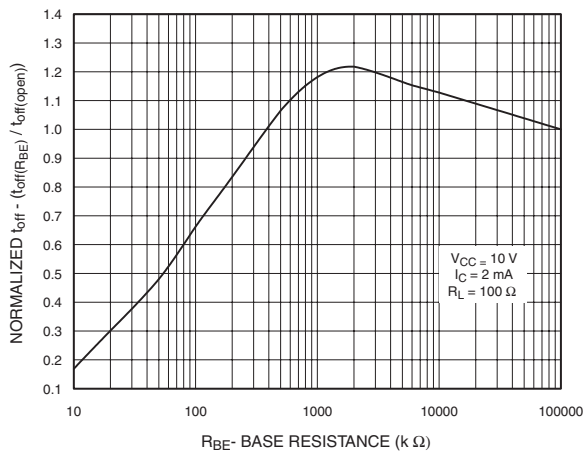


Fig. 10 Dark Current vs. Ambient Temperature

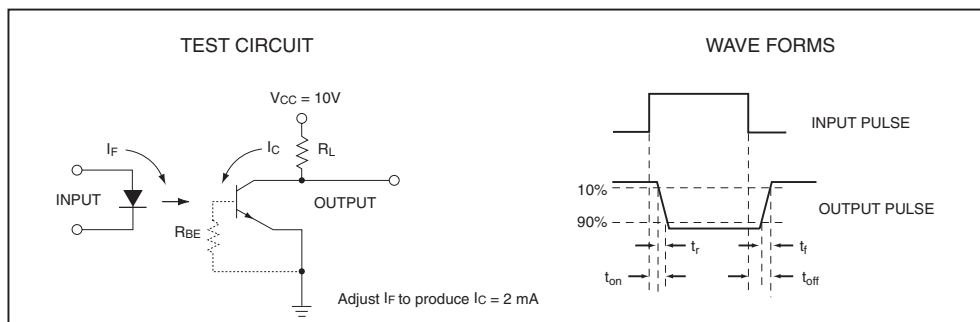
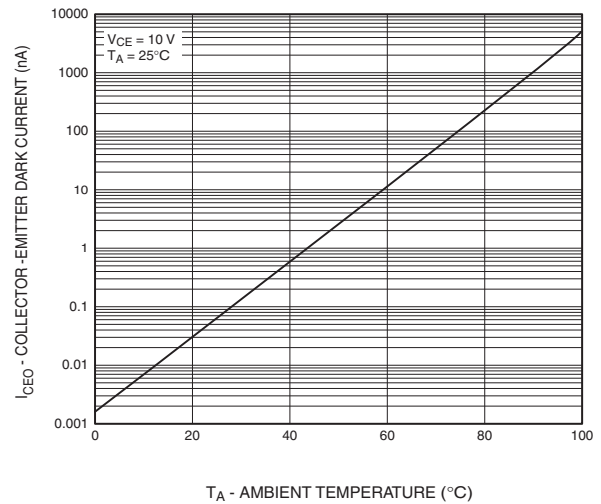


Figure 11. Switching Time Test Circuit and Waveforms

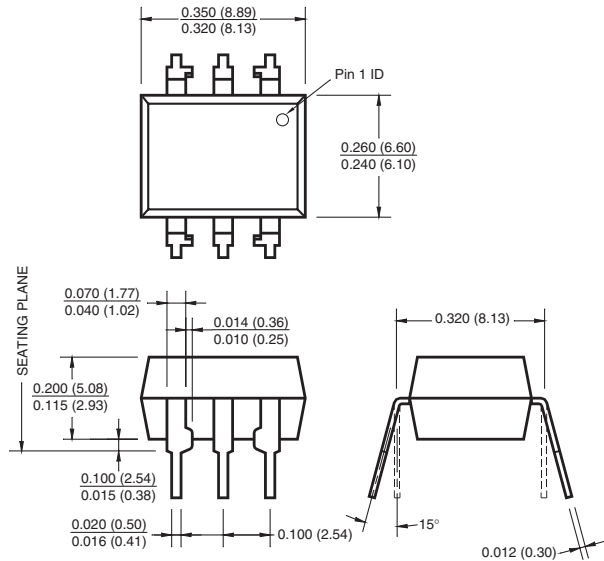
H11AV1-M

H11AV1A-M

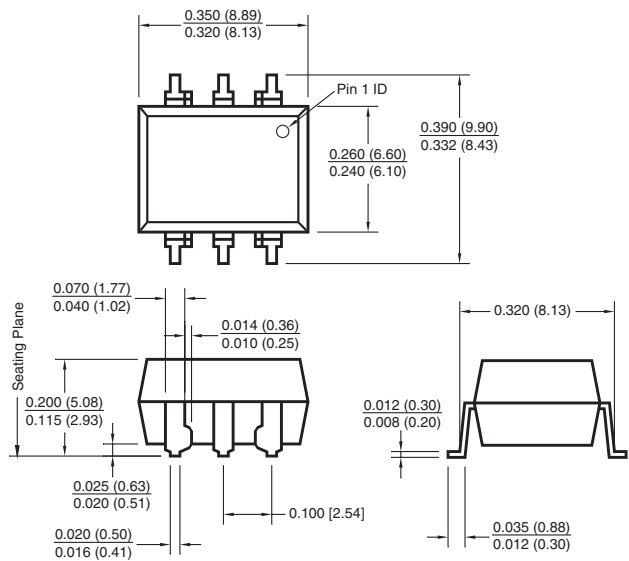
H11AV2-M

H11AV2A-M

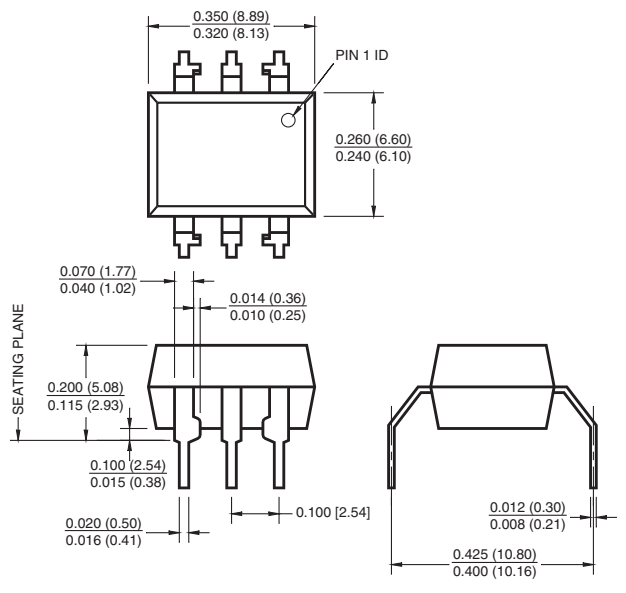
Package Dimensions (Through Hole)



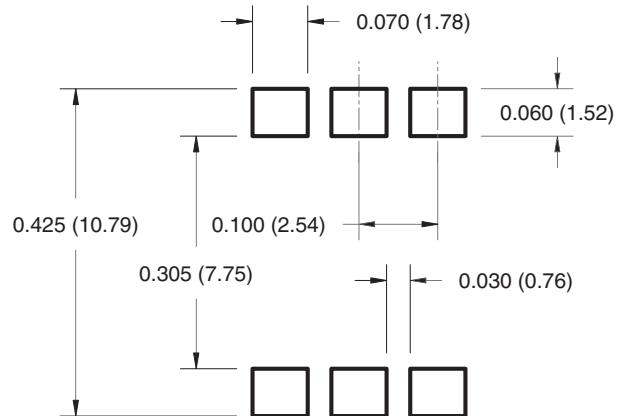
Package Dimensions (Surface Mount)



Package Dimensions (0.4" Lead Spacing)



Recommended Pad Layout for Surface Mount Leadform



NOTE

All dimensions are in inches (millimeters)

H11AV1-M

H11AV1A-M

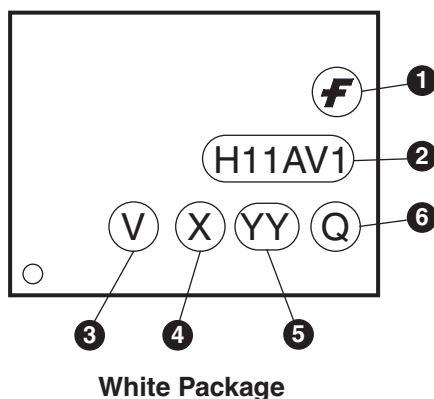
H11AV2-M

H11AV2A-M

ORDERING INFORMATION

| Order Entry Identifier | | |
|------------------------|--------------------------------------|--------------|
| Order Entry Identifier | Option | Example |
| S | Surface Mount Lead Bend | H11AV1S-M |
| SR2 | Surface Mount; Tape and reel | H11AV1SR2-M |
| N/A | 0.4" Lead Spacing | H11AV1A-M |
| V | VDE 0884 | H11AV1V-M |
| N/A | VDE 0884, 0.4" Lead Spacing | H11AV1AV-M |
| SV | VDE 0884, Surface Mount | H11AV1SV-M |
| SR2V | VDE 0884, Surface Mount, Tape & Reel | H11AV1SR2V-M |

MARKING INFORMATION



| Definitions | |
|-------------|--|
| 1 | Fairchild logo |
| 2 | Device number |
| 3 | VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table) |
| 4 | One digit year code • One digit for white package parts, e.g., '3' |
| 5 | Two digit work week ranging from '01' to '53' |
| 6 | Assembly package code |

*Note – Parts built in the white package (M suffix) that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in the portrait format.

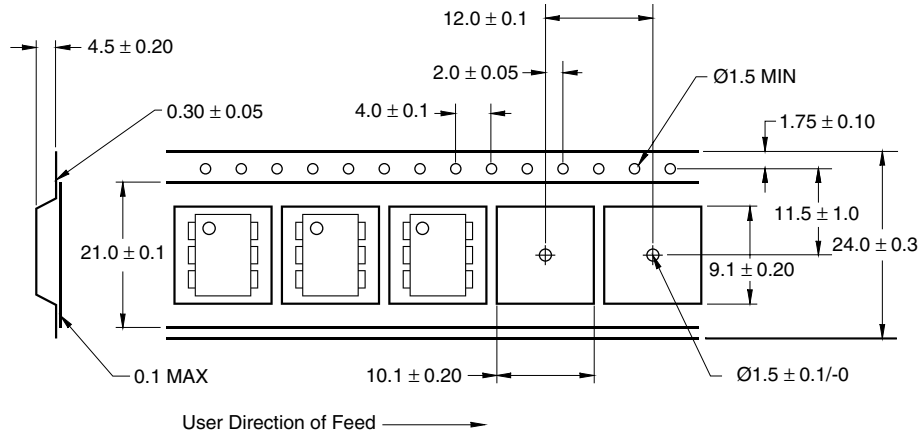
H11AV1-M

H11AV1A-M

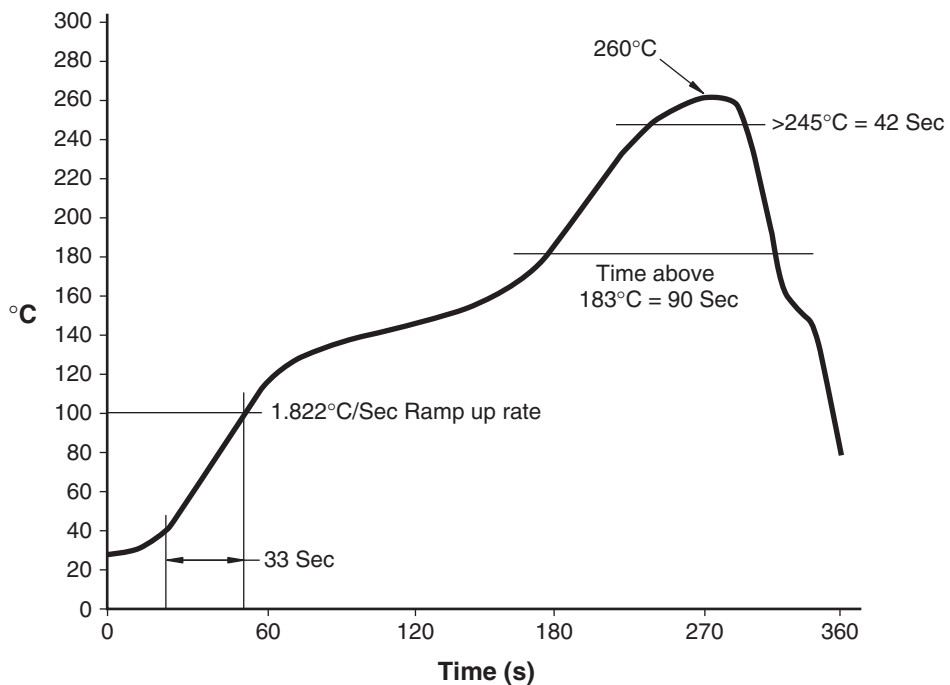
H11AV2-M

H11AV2A-M

Carrier Tape Specifications



Reflow Profile



H11AV1-M

H11AV1A-M

H11AV2-M

H11AV2A-M

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